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Memory Products	

82S191 / 82S191A

16K-bit TTL bipolar PROM

DESCRIPTION

The 82S191 and 82S191A are field programmable, which means that custom patterns are immediately available by following the Signetics Generic I fusing procedure. The 82S191 and 82S191A are supplied with all outputs at logical Low. Outputs are programmed to a logic High level at any specified address by fusing the Ni-Cr link matrix.

This device includes on-chip decoding and 3 Chip Enable inputs for ease of memory expansion. It features 3-State outputs for optimization of word expansion in bused organizations.

Ordering information can be found on the following page.

The 82S191 and 82S191A devices are also processed to military requirements for operation over the military temperature range. For specifications and ordering information consult the Signetics Military Data Handbook.

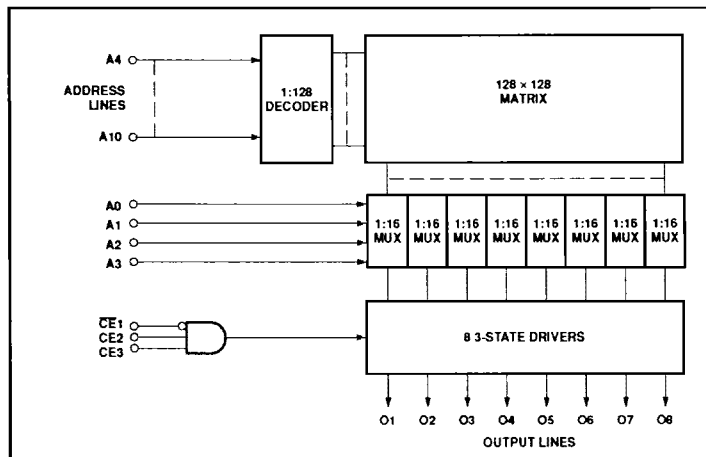
FEATURES

- Address access time:
 - N82S191: 80ns max
 - N82S191A: 55ns max
- Power dissipation: 40μW/bit typ
- Input loading: -100μA max
- Three Chip Enable inputs
- On-chip address decoding
- No separate fusing pins
- Unprogrammed outputs are Low level
- Fully TTL compatible
- Outputs: 3-State

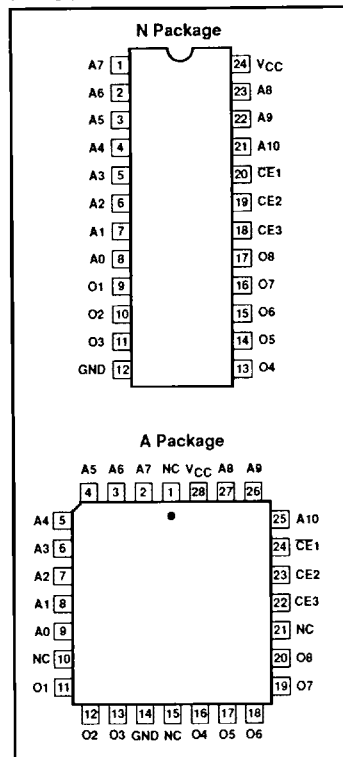
APPLICATIONS

- Sequential controllers
- Microprogramming
- Hardwired algorithms
- Control store
- Random logic
- Code conversion

BLOCK DIAGRAM



PIN CONFIGURATIONS



16K-bit TTL bipolar PROM (2048 × 8)

82S191 / 82S191A

ORDERING INFORMATION

DESCRIPTION	ORDER CODE
24-Pin Plastic Dual-In-Line 600mil-wide	N82S191 N, N82S191A N
28-Pin Plastic Leaded Chip Carrier 450mil-square	N82S191 A, N82S191A A

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING	UNIT
V_{CC}	Supply voltage	+7.0	V_{DC}
V_{IN}	Input voltage	+5.5	V_{DC}
V_O	Output voltage Off-State	+5.5	V_{DC}
T_{amb}	Operating temperature range	0 to +75	°C
T_{stg}	Storage temperature range	-65 to +150	°C

DC ELECTRICAL CHARACTERISTICS

0°C ≤ T_{amb} ≤ +75°C, 4.75V ≤ V_{CC} ≤ 5.25V

SYMBOL	PARAMETER	TEST CONDITIONS ^{1,2}	LIMITS			UNIT	
			Min	Typ ³	Max		
Input voltage							
V_{IL}	Low	$I_{IN} = -12mA$	2.0		0.8	V	
V_{IH}	High				-0.8	V	
V_{IC}	Clamp				-1.2	V	
Output voltage							
V_{OL}	Low	CE1 = Low, CE2,3 = High $I_{OUT} = 9.6mA$ $I_{OUT} = -2.0mA$	2.4		0.45	V	
V_{OH}	High				V		
Input current¹							
I_{IL}	Low	$V_{IN} = 0.45V$ $V_{IN} = 5.5V$			-100	μA	
I_{IH}	High				40	μA	
Output current¹							
I_{OZ}	Hi-Z state	CE1 = High, CE2,3 = Low, $V_{OUT} = 0.5V$ CE1 = High, CE2,3 = Low, $V_{OUT} = 5.5V$ CE1 = Low, CE2,3 = High, $V_{OUT} = 0V$			-40	μA	
I_{OS}	Short circuit ⁴				40	μA	
					-70	mA	
Supply current⁵							
I_{CC}		$V_{CC} = 5.25V$			130	175	mA
Capacitance							
C_{IN}	Input	CE1 = High, CE2,3 = Low, $V_{CC} = 5.0V$ $V_{IN} = 2.0V$ $V_{OUT} = 2.0V$			5		pF
C_{OUT}	Output				8		pF

NOTES:

- Positive current is defined as into the terminal referenced.
- All voltages with respect to network ground.
- Typical values are at $V_{CC} = 5V$, $T_{amb} = +25°C$.
- Duration of the short circuit should not exceed 1 second.
- Measured with all inputs grounded and all outputs open.

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AC ELECTRICAL CHARACTERISTICS

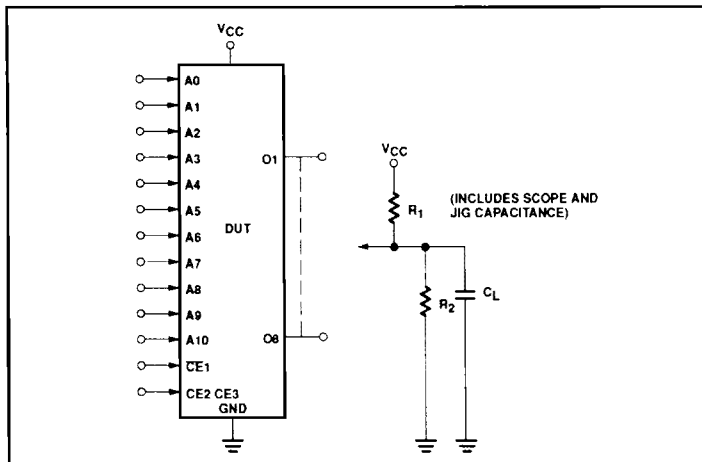
$R_1 = 470\Omega$, $R_2 = 1k\Omega$, $C_L = 30pF$, $0^\circ C \leq T_{amb} \leq +75^\circ C$, $4.75V \leq V_{CC} \leq 5.25V$

SYMBOL	PARAMETER	TO	FROM	N82S191			N82S191A			UNIT
				Min	Typ ¹	Max	Min	Typ ¹	Max	
Access time²										
t_{AA}		Output	Address		50	80		50	55	ns
t_{CE}		Output	Chip Enable		30	40		20	30	ns
Disable time³										
t_{CD}		Output	Chip Disable		30	40		20	30	ns

NOTES:

1. Typical values are $V_{CC} = 5V$, $T_{amb} = +25^\circ C$.
2. Tested at an address cycle time of $1\mu s$.
3. Measured at a delta of 0.5V from Logic Level with $R_1 = 750\Omega$, $R_2 = 750\Omega$ and $C_L = 5pF$.

TEST LOAD CIRCUIT



VOLTAGE WAVEFORM

